

Docket No.
11675.168

Total Pages in this Submission

UTILITY PATENT APPLICATION TRANSMITTAL
(Large Entity)*(Only for new nonprovisional applications under 37 CFR 1.53(b))***TO THE ASSISTANT COMMISSIONER FOR PATENTS**Box Patent Application
Washington, D.C. 20231

Transmitted herewith for filing under 35 U.S.C. 111(a) and 37 C.F.R. 1.53(b) is a new utility patent application for an invention entitled:

THERMALLY CONDUCTIVE INTERPOSER AND METHOD

and invented by:

Leonard E. Mess

If a **CONTINUATION APPLICATION**, check appropriate box and supply the requisite information:☐ Continuation ☐ Divisional ☐ Continuation-in-part (CIP) of prior application No.: _____

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Enclosed are:

Application Elements

1. ☒ Filing fee as calculated and transmitted as described below
2. ☒ Specification having 32 pages and including the following:
 - a. ☒ Descriptive Title of the Invention
 - b. ☐ Cross References to Related Applications *(if applicable)*
 - c. ☐ Statement Regarding Federally-sponsored Research/Development *(if applicable)*
 - d. ☐ Reference to Microfiche Appendix *(if applicable)*
 - e. ☒ Background of the Invention
 - f. ☒ Brief Summary of the Invention
 - g. ☒ Brief Description of the Drawings *(if drawings filed)*
 - h. ☒ Detailed Description
 - i. ☒ Claim(s) as Classified Below
 - j. ☒ Abstract of the Disclosure

UTILITY PATENT APPLICATION TRANSMITTAL (Large Entity)

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Application Elements (Continued)

3. ☒ Drawing(s) (when necessary as prescribed by 35 USC 113)
- a. ☒ Formal Number of Sheets 4
- b. ☐ Informal Number of Sheets _____
4. ☒ Oath or Declaration
- a. ☒ Newly executed (original or copy) ☐ Unexecuted
- b. ☐ Copy from a prior application (37 CFR 1.63(d)) (for continuation/divisional application only)
- c. ☒ With Power of Attorney ☐ Without Power of Attorney
- d. ☐ DELETION OF INVENTOR(S)
Signed statement attached deleting inventor(s) named in the prior application,
see 37 C.F.R. 1.63(d)(2) and 1.33(b).
5. ☐ Incorporation By Reference (usable if Box 4b is checked)
The entire disclosure of the prior application, from which a copy of the oath or declaration is supplied under
Box 4b, is considered as being part of the disclosure of the accompanying application and is hereby
incorporated by reference therein.
6. ☐ Computer Program in Microfiche (Appendix)
7. ☐ Nucleotide and/or Amino Acid Sequence Submission (if applicable, all must be included)
- a. ☐ Paper Copy
- b. ☐ Computer Readable Copy (identical to computer copy)
- c. ☐ Statement Verifying Identical Paper and Computer Readable Copy

Accompanying Application Parts

8. ☒ Assignment Papers (cover sheet & document(s))
9. ☐ 37 CFR 3.73(B) Statement (when there is an assignee)
10. ☐ English Translation Document (if applicable)
11. ☐ Information Disclosure Statement/PTO-1449 ☐ Copies of IDS Citations
12. ☐ Preliminary Amendment
13. ☒ Acknowledgment postcard
14. ☒ Certificate of Mailing

☐ First Class ☒ Express Mail (Specify Label No.): EM521656714US

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Accompanying Application Parts (Continued)

15. ☐ Certified Copy of Priority Document(s) (if foreign priority is claimed)
16. ☐ Additional Enclosures (please identify below):

Fee Calculation and Transmittal

CLAIMS AS FILED

For	#Filed	#Allowed	#Extra	Rate	Fee
Total Claims	38	- 20 =	18	x \$22.00	\$396.00
Indep. Claims	12	- 3 =	9	x \$82.00	\$738.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
BASIC FEE					\$790.00
OTHER FEE (specify purpose) Assignment Recordal					\$40.00
TOTAL FILING FEE					\$1,964.00

- ☒ A check in the amount of \$1,964.00 to cover the filing fee is enclosed.
- ☐ The Commissioner is hereby authorized to charge and credit Deposit Account No. as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of as filing fee.
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- ☒ Charge any additional filing fees required under 37 C.F.R. 1.16 and 1.17.
- ☒ Charge the issue fee set in 37 C.F.R. 1.18 at the mailing of the Notice of Allowance, pursuant to 37 C.F.R. 1.311(b).


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PATENT APPLICATION
Docket No. 11675.168

UNITED STATES PATENT APPLICATION

of

LEONARD E. MESS

for

THERMALLY CONDUCTIVE INTERPOSER AND METHOD

BACKGROUND OF THE INVENTION

1. The Field of the Invention

This invention is in the field of semiconductive device technology. More specifically, this invention is in the field of interposers for electrically connecting semiconductive devices to an electrical apparatus.

2. The Relevant Technology

A semiconductive device is often electrically coupled to an electrical apparatus such as a computer through the use of an interposer. In one such process, the semiconductive device is connected to the interposer, which is then inserted into the socket of the electrical apparatus. The socket may be mounted on the motherboard of a computer, for example. Thus, the semiconductive device communicates electrically through the interposer with the electrical apparatus. Typical interposers currently employed in the coupling of semiconductive devices to electrical apparatuses are comprised of an FR4 fiberglass material, or the like, having electrically conductive metal lines or traces thereon.

The term "semiconductive device" extends to any device or assembly that includes circuitry defined in a semiconductive material, and further extends to a chip package that includes semiconductive material. The external and additional structure of a package assembly may be used, for example, for mounting the semiconductive device to a printed circuit board or other external circuitry, for establishing electrical connection between the semiconductive device and external circuitry, for improving the ease of handling or transporting the semiconductive device, and/or for protecting the semiconductive device from environmental conditions. Many chip packages include a lead frame that extends beyond the body thereof. The lead frame typically includes an array of electrical leads that extend from the internal circuitry of the integrated circuit to the exterior portion of the chip package where they are exposed to the surroundings.

As a result of this thermal expansion incompatibility, shear stresses develop in the interface between the interposer and the semiconductive device when the semiconductive device becomes hot. These shear stresses can result in a severing of the electrical connection between the interposer and the semiconductive device. While it is possible to ameliorate the effects of shearing through a process known as wire bonding, this process adds additional

1 complexity and expense. Furthermore, the organic material within FR4 fiberglass interposers
2 absorbs moisture, causing the interposers to degrade.

3 There is therefore a need in the art for an improved interposer which assists in
4 protecting a semiconductive device coupled to the interposer from the potential damage
5 caused by significant amounts of heat generated by the semiconductive device. There is also
6 a need in the art for an improved interposer which prevents shear stress from severing the
7 electrical connection between the interposer and the semiconductive device.

SUMMARY OF THE INVENTION

An interposer of the present invention is comprised of (i) a substrate comprised of an electrically insulating, thermally conductive ceramic material; and (ii) an electrical conductor on the substrate having a receiving end for connecting to a semiconductive device and a terminal end for connecting to an electrical apparatus. The semiconductive device is electrically coupled to the electrical apparatus when the semiconductive device is connected to the receiving end of the electrical conductor and the terminal end of the electrical conductor is connected to the electrical apparatus. The invention also includes thermally conductive connections between the semiconductive device and an interposer.

In one embodiment, a thermally conductive connector connects the semiconductive device, such as an SRAM, DRAM, or integrated circuit device, to the interposer such that a portion of the semiconductive device is exposed to the atmosphere to thereby dissipate heat to the atmosphere. Both the thermally conductive interposer and the thermally conductive connector act as heat sinks to conduct heat from the semiconductive device to the ambient, thereby protecting the semiconductive device from overheating. The interposer preferably has a coefficient of thermal expansion which is substantially similar to the coefficient of thermal expansion of a semiconductive device on the interposer, thereby preventing shearing of the electrical connection between the semiconductive device and the interposer.

In one embodiment, the semiconductive device is fastened temporarily and removably to the interposer and the interposer is coupled to an electrical apparatus. In another embodiment, the semiconductive device is permanently coupled to the interposer. As an example of a connector, a biasing clip enables quick and convenient placement and removal of semiconductive devices on the interposer. The interposer may be permanently or removably coupled to the electrical apparatus, depending on the desired application.

1 These and other features of the present invention will become more fully apparent
2 from the following description and appended claims, or may be learned by the practice of the
3 invention as set forth hereinafter.

1 **BRIEF DESCRIPTION OF THE DRAWINGS**

2 In order that the manner in which the above-recited and other advantages of the
3 invention are obtained, a more particular description of the invention briefly described above
4 will be rendered by reference to specific embodiments thereof which are illustrated in the
5 appended drawings. Understanding that these drawings depict only typical embodiments of
6 the invention and are not therefore to be considered to be limiting of its scope, the invention
7 will be described and explained with additional specificity and detail through the use of the
8 accompanying drawings in which:

9 Figure 1 is a perspective view of an interposer kit of the present invention showing
10 one trace array empty, one trace array having a semiconductive device thereon, and one trace
11 array having a semiconductive device thereon with a biasing connector coupling the
12 semiconductive device to the interposer.

13 Figure 2 is a bottom surface view of a semiconductive device.

14 Figure 3 is a perspective view of a biasing connector of the present invention.

15 Figure 4 is a perspective view of another embodiment of a biasing connector of the
16 present invention.

17 Figure 5 is a perspective view of the interposer kit shown in Figure 1 with an
18 additional biasing connector and semiconductive device placed thereon.

19 Figure 6 is a cross-sectional, cut-away view of the semiconductive device and the
20 interposer shown in Figure 1.

21 Figure 7 is a cross-sectional, cut-away view of another embodiment of a
22 semiconductive device and interposer.

23 Figure 8 is a cross sectional, cut away view of the interposer of Figure 1 having an
24 insulating layer on the intermediate portion of a conductor thereof.

25 Figure 9 is a schematic view of an electrical apparatus shown as receiving the
26 interposer kit shown in Figure 5.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

With reference now to Figures 1 and 2, the present invention relates to an interposer system 10 comprising (i) an interposer 12; and (ii) a connector 14 for connecting a semiconductive device 16 to interposer 12. Interposer 12 is configured to electrically couple semiconductive device 16 to an electrical apparatus (not shown in Fig. 1), such as a testing apparatus which monitors, tests or evaluates device 16, by for example storing information on device 16 and retrieving information from device 16.

Interposer 12 is electrically coupled to the electrical connections 17 of device 16, the bottom surface of which is shown in Figure 2, and to electrical connections on an electrical apparatus, thereby electrically coupling semiconductive device 16 to the electrical apparatus. By coupling semiconductive devices 16 on interposer 12, and coupling interposer 12 to the electrical apparatus, the electrical apparatus may perform a variety of functions upon the semiconductive devices, while the semiconductive devices are protected from overheating by the heat dissipating qualities of interposer 12.

Interposer 12 and preferably, connector 14, are thermally conductive. As shown in Figure 1, system 10 preferably exposes semiconductive device 16 partially to the open atmosphere, rather than completely covering devices 16 with a connector, allowing heat to dissipate to the atmosphere directly from semiconductive device 16. In addition, heat is transferred through thermally conductive interposer 12 and connector 14 from semiconductive device 16, then dissipated to the atmosphere. The thermal conductivity of interposer 12 and connector 14, along with the configuration of interposer 12 and connector 14 are significant advantages within the art.

Interposer 12 will now be discussed in additional detail. Interposer 12 is comprised of a substrate 18 and a plurality of electrical conductors 20 on substrate 18. Substrate 18 is comprised of an electrically insulating material. Substrate 18 also conducts heat, thereby dissipating heat away from device 16 connected to substrate 18. When exposed to the high

1 temperatures generated by advanced high density, high integration devices 16, substrate 18
2 does not warp or bow. Substrate 18 has formed thereon electrical conductors 20, such as
3 metal traces. Substrate 18 also preferably has substantially similar thermal expansion
4 properties as semiconductor device 16, such as a substantially similar coefficient of thermal
5 expansion as that of semiconductive device 16. By having substantially similar thermal
6 expansion properties, shear stress is reduced in the physical connections between device 16
7 and interposer 12 so as to prevent a severing of the electrical connection between device 16
8 and interposer 12.

9 In one embodiment, substrate 18 is comprised of a ceramic material, such as an
10 inorganic ceramic material. Examples of ceramic materials used in the production of
11 substrate 18 include glass. Many forms of glass may be used, including glass comprising
12 silicates, silica, silicon oxide, phosphates, or borates, or derivatives thereof. Such glass may
13 be doped with metal, an oxide or other elements, so long as it remains electrically insulative.
14 Glass may be formed by fusing silica with a basic oxide, for example. Borophosphosilicate
15 glass is one example of a material useful for substrate 18. Inorganic forms of glass are
16 preferable. Glass materials often have substantially similar thermal expansion properties as
17 semiconductive devices 16, which are often substantially comprised in the most part of
18 silicon or other semiconductive material.

19 In addition to glass, other ceramics useful in the present invention as substrate 18
20 include alumina, aluminum nitrides, nonmetallic nitrides, nonmetallic carbides, single oxide
21 ceramics, mixed oxide ceramics, and mixtures and derivatives thereof. As used throughout
22 this specification and the appended claims, the term "nonmetallic nitrides" includes boron
23 nitrides, silicon nitrides and other transitional element nitrides. Alumina, for example, may
24 be used alone or in combination with silica or silicates, for example, because alumina resists
25 harsh environments and also dissipates heat.

An interposer of the present invention may comprise a single conductor or a plurality of conductors. The interposer may have a single array of conductors or may have a plurality of arrays, such as arrays 22, 24, 26 as shown in Figure 1. Each array may have as many conductors as needed to electrically couple a particular semiconductive device, such as device 16, to an electrical apparatus. Conductors may have a variety of different

1 configurations any of which are designed to electrically couple a semiconductive device to
2 an electrical apparatus. Heat dissipates to the environment through the conductors and from
3 the conductors through the substrate to the ambient.

4 In one embodiment, the semiconductive device is permanently coupled to the
5 interposer. The semiconductive device may be permanently coupled to the interposer
6 through the use of an adhesive, for example, which is another example of a connector. In an
7 underfilling process, adhesive is placed around the edges of semiconductive device 16
8 mounted on interposer 12, then the adhesive is permitted to wick through capillary action
9 between interposer 12 and semiconductive device 16. This process can be repeated until the
10 desired bond is achieved between interposer 12 and the semiconductive device 16. This
11 underfilling process is often used for flip chips, for example. Preferably, the adhesive is a
12 thermally conductive adhesive, such as a silver-filled epoxy, or a tape having acrylics filled
13 with alumina or aluminum nitride with a matrix in resin. The thermally conductive adhesive
14 enhances heat dissipation away from semiconductive device 16. Adhesives may be applied
15 using a screen printing process, for example.

16 In another embodiment, semiconductive device 16 is removably coupled to
17 interposer 12, such as when it is desired to test device 16 by coupling device 16 to testing
18 apparatus which monitors, tests, and/or evaluates device 16. Preferably, when removability
19 is desired, connectors such as resilient biasing connectors 14 are employed. As shown in
20 Figure 1, biasing connector 14 connects device to interposer 12 such that a substantial
21 portion of device 16 is exposed to the open environment, thereby assisting in dissipating heat
22 from device 16.

23 With reference now to Figures 3, 4, and 5, various embodiments of biasing
24 connectors are demonstrated. As shown in Figure 3, connector 14 comprises a resilient clip
25 having a top plate 38, a bottom plate 40, and an intermediate portion 42 coupling top plate

1 38 to bottom plate 40. Connector 14 may be employed to resiliently, removably bias
2 semiconductive device 16 against interposer 12.

3 Another embodiment of a connector 44 is demonstrated in Figure 4. Connector 44
4 comprises a resilient clip having an upper plate 46, a lower plate 48 and an intermediate
5 portion 50 coupling upper plate 46 to lower plate 48. Each of plates 46, 48 include a bow
6 in the central portion thereof. The bow in plates 46, 48 allowing front ends 52, 54 of clip
7 44 to be readily biased open and closed manually for placement over device 16 and substrate
8 12.

9 As shown in Figure 5, in one embodiment one connector 14 is used for a single
10 semiconductive device 16, whereas in another embodiment a single connector 56 is used to
11 couple a plurality of semiconductive devices 16 to interposer 12. Connector 56 may be in
12 the shape of clip 14, clip 44, or a variety of other clips or other configurations. A variety of
13 different designs of connectors may be employed in the present invention such as other clips,
14 crimps, clamps and a variety of other connectors having shapes and configurations which
15 allow them to resiliently, removably bias semiconductive devices 16 to interposer 12.

16 In a preferred embodiment, heat is also conducted through a thermally conductive
17 connector to the environment. Biasing connectors 14, 44, and 56 are preferably comprised
18 of a resilient, heat dissipating material such as copper, copper alloy, or another metal. The
19 connectors are also insulated from the electrical connections on devices 16, such as by being
20 further comprised of or coated with an electrically insulating material, such as glass or
21 polymer or by being placed on electrically insulating portions of devices 16. The connectors
22 thus resiliently, removably bias semiconductive devices 16 against interposer 12 while
23 simultaneously assisting in dissipating the heat generated by devices 16 in conducting the
24 heat to the atmosphere. These connectors do so in a manner which allows a portion of the
25 device itself to be exposed to the atmosphere, thereby increasing the dissipative qualities of
26 system 10.

As shown in Figure 6, in one embodiment, electrical conductor 20 has a bumped receiving end 28 which projects from the upper surface of substrate 18. In this embodiment, semiconductive device 16 includes a corresponding electrical conductor 32 having a bumped

1 terminal 30 which couples to receiving end 28, thereby forming a connection between bump
2 30 and bump 28 when device 16 and interposer 12 are connected together such that bumps
3 28 and 30 interface. This creates a physical connection between substrate 18 and device 16.
4 This configuration allows bumps 28, 30 to slide against one another, permitting convenient
5 coupling of bumps 28, 30 together as well as removal of bumps 28, 30 one from another.

6 In another embodiment, as shown in Figure 7, the electrical connection between an
7 interposer 59 and a semiconductive device 58 is created by providing for a complimentary,
8 male/female connection between device 58 and interposer 59. Although interposer 59 is
9 shown as comprising the female fitting, the interposer may comprise the male fitting, as
10 shown in Figure 6 with protruding bumped receiving end 28, while the semiconductive
11 device comprises the female fitting which is formed in a recess of the semiconductive device.

12 In the embodiment shown in Figure 7, interposer 59 comprises a substrate 60 having
13 a recess 62 therein. A conductor 64 such as a metal trace is placed on substrate 60 such that
14 a receiving end 66 of conductor 64 is disposed within recess 62, which is below the upper
15 surface of substrate 60, allowing a male connecting terminal 68 of a conductor on
16 semiconductive device 58 to be electrically coupled with receiving end 66 by being placed
17 therein. Conductor 64 also has a terminal end (not shown) for connecting to an electrical
18 apparatus. A connector such as connector 14, 44, or 56 may then be placed to bias device
19 58 towards substrate 60 to thereby retain the electrical connection between bump 68 and
20 recessed receiving end 66. It will be appreciated that the male/female complimentary fit
21 shown in Figure 7 would be advantageous because of the structural integrity and non-slip
22 design derived therefrom.

23 According to one method of manufacturing interposer 12 or 59, a substrate 18 or 60
24 of the present invention is provided comprising a ceramic material. At least one electrical
25 conductor 20 or 64 is then coupled onto the substrate. In one embodiment, recess 62 is
26 formed within substrate 60, such as through etching, and at least a portion of conductor 64

1 is placed within the recess 62. A recess may be formed to receive receiving end 66, as shown
2 in Figure 7, the entire conductor, an intermediate portion of conductor 64 and end 66, or a
3 variety of other portions of conductor 64.

4 As yet another feature of the invention, as shown in Figure 8, it is possible to form
5 a layer 69, such as a coating, of an electrically insulating material on the intermediate
6 portion 36 of electrical conductor 20 of interposer 12. The electrically insulating material
7 for layer 69 may comprise an electrically insulating material, such as a polymer or resin. In
8 one embodiment, the electrically insulating material is thermally conductive, such as a
9 ceramic material such as described above (e.g., glass, aluminum nitride or alumina), for
10 example. Thus, in one embodiment, layer 69 electrically insulates conductor 20 from contact
11 with an electrical conductor, such as an uninsulated connector, and simultaneously aids in
12 heat dissipation.

13 With reference now to Figure 9, interposer 12 having semiconductive devices 16
14 electrically coupled thereto through the use of connectors 14, 56 is electrically coupled to an
15 electrical apparatus 70 such as a testing apparatus shown in a diagrammatic view in Figure 9.
16 Interposer 12 may be permanently or removably coupled to apparatus 70.

17 As used throughout this specification and the appended claims, the term "electrical
18 apparatus" refers to an apparatus which electrically couples to a semiconductive device.
19 Examples of such apparatuses include a computer, program logic controller, electronic game
20 assembly, a controlling module, and a testing apparatus which monitors, tests, or evaluates
21 a semiconductive device. The testing apparatus may be a computerized testing apparatus,
22 for example.

23 Apparatus 70 includes a socket, such as a printed circuit board socket, having
24 electrical terminals onto which terminal ends 34 of conductors 20 of interposer 12 are placed.
25 After terminal ends 34 of interposer 12 are placed into the socket, an electrical connection

1 exists between semiconductive devices 16 and apparatus 70, thereby allowing a user to test
2 device 16 or otherwise engage in a variety of different functions.

3 Thus, one method for testing semiconductive device comprises providing an
4 interposer having substrate comprised of an electrically insulating, thermally conductive
5 ceramic material, electrically coupling the interposed to a semiconductive device, electrically
6 coupling the interposer to a testing apparatus such that the testing apparatus is electrically
7 coupled to semiconductive device, and then actuating the testing apparatus to electrically
8 communicate with the semiconductive device.

9 A variety of different semiconductive devices may be electrically coupled to the
10 inventive interposer. Examples of such semiconductive devices include DRAMs, SRAMs,
11 integrated circuit devices, and the like, each of which has electrical conductors thereon such
12 as bumps, lead fingers, or other package connections. The semiconductive devices, however,
13 may be either packaged or non-packaged.

14 The present invention may be embodied in other specific forms without departing
15 from its spirit or essential characteristics. The described embodiments are to be considered
16 in all respects only as illustrative and not restrictive. The scope of the invention is, therefore,
17 indicated by the appended claims rather than by the foregoing description. All changes
18 which come within the meaning and range of equivalency of the claims are to be embraced
19 within their scope.

20 What is claimed and desired to be secured by United States Letters Patent is:

1 1. An interposer for electrically coupling a semiconductive device to an
2 electrical apparatus, the interposer comprising:

3 a substrate comprised of an electrically insulating, ceramic material; and
4 an electrical conductor on the substrate, the electrical conductor having a
5 receiving end for connecting to a semiconductive device and a terminal end for
6 connecting to an electrical apparatus.

7
8 2. An interposer as recited in claim 1, wherein the substrate comprises a
9 substantially planar sheet.

10
11 3. An interposer as recited in claim 1, wherein the substrate comprises a
12 substantially homogenous material.

13
14 4. An interposer as recited in claim 1, wherein the receiving end protrudes
15 upwardly with respect to the substrate.

16
17 5. An interposer as recited in claim 1, wherein the receiving end is disposed
18 within a recess in the substrate.

19
20 6. An interposer as recited in claim 1, wherein the substrate comprises a material
21 selected from the group consisting of glass, alumina, glass ceramic, nonmetallic nitride,
22 aluminum nitride, nonmetallic carbide, and mixtures and derivatives thereof.

23
24 7. An interposer as recited in claim 1, wherein the substrate comprises boron
25 nitride.

26

1 8. An interposer as recited in claim 1, wherein the interposer further comprises
2 an electrically insulating layer on a portion of the conductor between the receiving end and
3 the terminal end.

4
5 9. An interposer as recited in claim 8, wherein the electrically insulating layer
6 comprises a thermally conductive material.

7

8

1 10. An interposer for electrically coupling a semiconductive device to an
2 electrical apparatus, the interposer comprising:

3 a substantially homogeneous, substantially planar sheet comprised of an
4 electrically insulating, inorganic ceramic material; and

5 an electrical conductor on the sheet, the electrical conductor having a
6 receiving end for connecting to a semiconductive device and a terminal end for
7 connecting to an electrical apparatus, such that the semiconductive device is
8 electrically coupled to the electrical apparatus when the semiconductive device is
9 connected to the receiving end of the electrical conductor and the terminal end of the
10 electrical conductor is connected to the electrical apparatus.

11
12 11. An interposer as recited in claim 10, wherein the substrate consists essentially
13 of alumina.

14
15 12. An interposer as recited in claim 10, wherein the substrate consists essentially
16 of a glass ceramic material.
17

1 13. An interposer for electrically coupling a semiconductive device to an
2 electrical apparatus, the interposer comprising:

3 a substantially homogeneous, substantially planar sheet composed of an
4 electrically insulating material selected from the group consisting of glass ceramics,
5 devitrified ceramics, vitro ceramics, alumina, single oxide ceramics, and mixed oxide
6 ceramics, and mixtures and derivatives thereof; and

7 an electrical conductor on the sheet, the electrical conductor having a
8 receiving end for connecting to a semiconductive device and a terminal end for
9 connecting to an electrical apparatus, such that the semiconductive device is
10 electrically coupled to the electrical apparatus when the semiconductive device is
11 connected to the receiving end of the electrical conductor and the terminal end of the
12 electrical conductor is connected to the electrical apparatus.
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a substantially homogeneous, substantially planar sheet composed of an electrically insulating material selected from the group consisting of alumina, alumina with silica, alumina with silicates, alumina with derivatives of silicates, and mixtures and derivatives thereof; and

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1 15. An interposer for electrically coupling a semiconductive device to an
2 electrical apparatus, the interposer comprising:

3 a substantially homogeneous, substantially planar sheet composed of an
4 electrically insulating material selected from the group consisting of boron nitrides,
5 aluminum nitrides, and mixtures and derivatives thereof; and

6 an electrical conductor on the sheet, the electrical conductor having a
7 receiving end for connecting to a semiconductive device and a terminal end for
8 connecting to an electrical apparatus, such that the semiconductive device is
9 electrically coupled to the electrical apparatus when the semiconductive device is
10 connected to the receiving end of the electrical conductor and the terminal end of the
11 electrical conductor is connected to the electrical apparatus.
12
13

1 16. An interposer for electrically coupling a semiconductive device to an
2 electrical apparatus, the interposer comprising:

3 a substantially homogeneous, substantially planar sheet composed of an
4 electrically insulating material selected from the group consisting of oxides of
5 silicon, silicate glass, and nucleated, substantially crystalline glass, and mixtures and
6 derivatives thereof; and

7 an electrical conductor on the sheet, the electrical conductor having a
8 receiving end for connecting to a semiconductive device and a terminal end for
9 connecting to an electrical apparatus, such that the semiconductive device is
10 electrically coupled to the electrical apparatus when the semiconductive device is
11 connected to the receiving end of the electrical conductor and the terminal end of the
12 electrical conductor is connected to the electrical apparatus.
13

1 17. A system for electrically coupling a semiconductive device to an electrical
2 apparatus, the system comprising:
3 an interposer, the interposer comprising:
4 a substrate comprised of an electrically insulating ceramic
5 material; and
6 a plurality of electrical conductors on the substrate, each
7 electrical conductor having a receiving end for connecting to a
8 semiconductive device and a terminal end for connecting to an
9 electrical apparatus, such that electrical circuitry within the
10 semiconductive device is electrically coupled to the electrical
11 apparatus when the semiconductive device is connected to said
12 plurality of receiving ends of the electrical conductors and said
13 plurality of terminal ends of the electrical conductors are connected
14 to the electrical apparatus; and
15 a connector for holding the semiconductive device stationary relative to the
16 interposer.

17
18 18. A system as recited in claim 17, wherein the connector connects the
19 semiconductive device to the interposer such that a portion of the semiconductive device is
20 exposed to the atmosphere to thereby dissipate heat to the atmosphere.

21
22 19. A system as recited in claim 17, wherein the connector removably connects
23 the semiconductive device to the interposer.

24
25 20. A system as recited in claim 17, wherein the connector comprises a resilient
26 biasing clip.

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21. A system as recited in claim 17, wherein the connector is composed of a metal al.

22. A system as recited in claim 17, wherein the connector comprises an adhesive.

23. A system as recited in claim 17, wherein at least one of said receiving ends is connected to the substrate.

24. A system as recited in claim 17, wherein at least one of said receiving ends is disposed within a recess in the substrate.

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1 28. A method for manufacturing an interposer for electrically coupling a
 2 semiconductive device to an electrical apparatus, comprising:

3 providing a substrate composed of an electrically insulating material selected
 4 from the group consisting of glass, alumina, glass ceramic, nonmetallic nitride,
 5 aluminum nitride, nonmetallic carbide, and mixtures and derivatives thereof;

6 forming a plurality of recesses in the substrate; and

7 forming a plurality of electrical conductors on the substrate, each electrical
 8 conductor having a receiving end for connecting to a semiconductive device and a
 9 terminal end for connecting to an electrical apparatus, such that the semiconductive
 10 device is electrically coupled to the electrical apparatus when the semiconductive
 11 device is connected to the receiving ends and the terminal ends are connected to the
 12 electrical apparatus, each receiving end being within one recess of said plurality of
 13 recesses.

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 15 29. A method as recited in claim 28, further comprising forming an electrically
 16 insulating material on each said electrical conductor between the receiving end thereof and
 17 the terminal end thereof.

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30. A method for testing a semiconductor device, comprising:

providing an electrical testing apparatus;

providing a container that contains a semiconductor device having electrical circuitry, the electrical circuitry being electrically connected to an electrical lead projecting out of the container;

providing an interposer comprising:

a substrate composed of an electrically insulating ceramic material, and

an electrical conductor on the substrate, the electrical conductor having a receiving end and a terminal end;

connecting the receiving end of the electrical conductor to the electrical lead of the semiconductor device;

connecting the terminal end of the electrical conductor to the electrical testing apparatus such that the electrical circuitry of the semiconductor device is in electrical communication with the electrical testing apparatus; and

performing an electrical test upon the electrical circuitry of the semiconductor device with the electrical testing apparatus.

1 31. A method for testing a semiconductive device, comprising:
2 providing an electrical testing apparatus;
3 providing a container that contains a semiconductor device having electrical
4 circuitry, the electrical circuitry being electrically connected to a plurality of electrical
5 leads projecting out of the container;
6 providing an interposer comprising:
7 a substrate composed of an electrically insulating ceramic
8 material, and
9 a plurality of electrical conductors on the substrate, each
10 electrical conductor having a receiving end and a terminal end;
11 connecting the receiving end of each electrical conductor to an electrical lead
12 of said plurality of the electrical leads;
13 connecting each terminal end of the plurality of electrical conductors to the
14 electrical testing apparatus such that the electrical circuitry of the semiconductive
15 device is in electrical communication with the electrical testing apparatus; and
16 performing an electrical test upon the electrical circuitry of the
17 semiconductive device with the electrical testing apparatus.
18

1 32. A method for testing a semiconductive device, comprising:
2 providing an electrical testing apparatus;
3 providing a semiconductive device having an electrical circuitry therein
4 electrically connected to an electrical lead projecting therefrom;
5 providing an interposer comprising:
6 a substrate composed of an electrically insulating material
7 selected from the group consisting of glass, alumina, glass ceramic,
8 nonmetallic nitride, aluminum nitride, nonmetallic carbide, and
9 mixtures and derivatives thereof; and
10 an electrical conductor on the substrate, the electrical
11 conductor having a receiving end and a terminal end;
12 connecting the receiving end of the electrical conductor to the electrical lead
13 of the semiconductive device;
14 connecting the terminal end of the electrical conductor to the electrical
15 testing apparatus such that the electrical circuitry of the semiconductive device is in
16 electrical communication with the electrical testing apparatus; and
17 performing an electrical test upon the electrical circuitry of the
18 semiconductive device with the electrical testing apparatus.

19
20 33. A method as defined in Claims 32, wherein connecting the receiving end of
21 the electrical conductor to the electrical lead of the semiconductive device comprises:
22 providing a connector for holding the interposer stationary relative to the
23 semiconductive device, the connector covering a portion of the semiconductive
24 device and another portion of the semiconductive device being exposed to the
25 ambient so as to dissipate heat thereto.
26

1 34. A method as defined in Claim 33, wherein the connector for biases the
2 receiving end of the electrical conductor to the electrical lead of the semiconductive device.

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4 35. A method as defined in Claim 33, wherein the connector is composed of a
5 ceramic material.

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7 36. A method as defined in Claim 33, wherein the connector comprises a resilient
8 biasing clip.

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10 37. A method as defined in Claim 33, wherein the connector is composed of metal
11 material.

12
13 38. A method as defined in Claim 32, wherein performing an electrical test upon
14 the electrical circuitry of the semiconductive device with the electrical testing apparatus
15 comprises:

16 the electrical testing apparatus storing information on the electrical circuitry
17 of the semiconductive device; and

18 the electrical testing apparatus retrieving the information from the electrical
19 circuitry of the semiconductive device.

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ABSTRACT OF THE INVENTION

An interposer for electrically coupling a semiconductive device to an electrical apparatus includes (i) a substrate comprised of an electrically insulating, thermally conductive ceramic material; and (ii) an electrical conductor on the substrate having a receiving end for connecting to a semiconductive device and a terminal end for connecting to an electrical apparatus. The semiconductive device is electrically coupled to the electrical apparatus when the semiconductive device is connected to the receiving end of the electrical conductor and the terminal end of the electrical conductor is connected to the electrical apparatus. A thermally conductive connector connects the semiconductive device to the interposer. The thermally conductive interposer and connector conduct heat from the semiconductive device to the environment, thereby protecting the semiconductive device from overheating.

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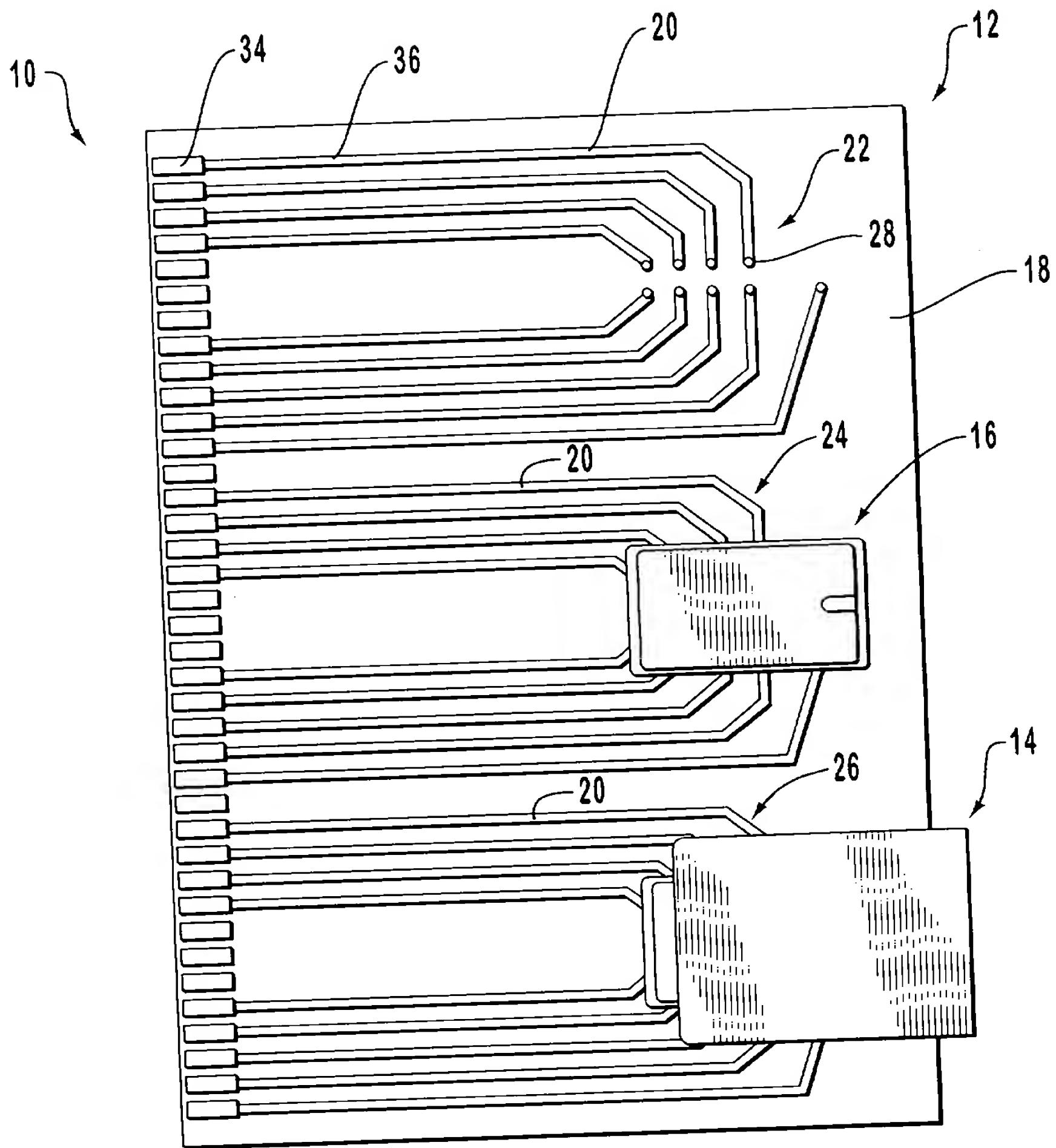


FIG. 1

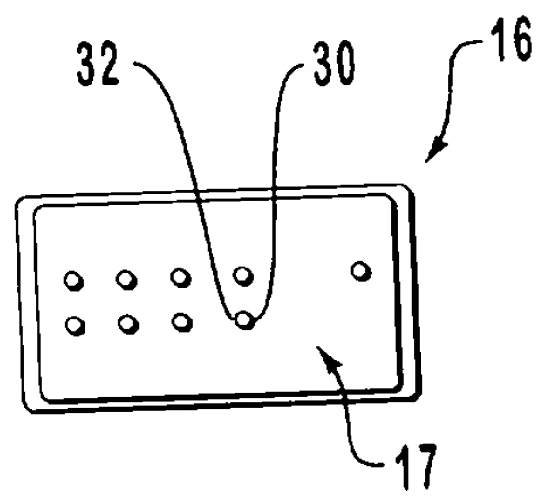


FIG. 2

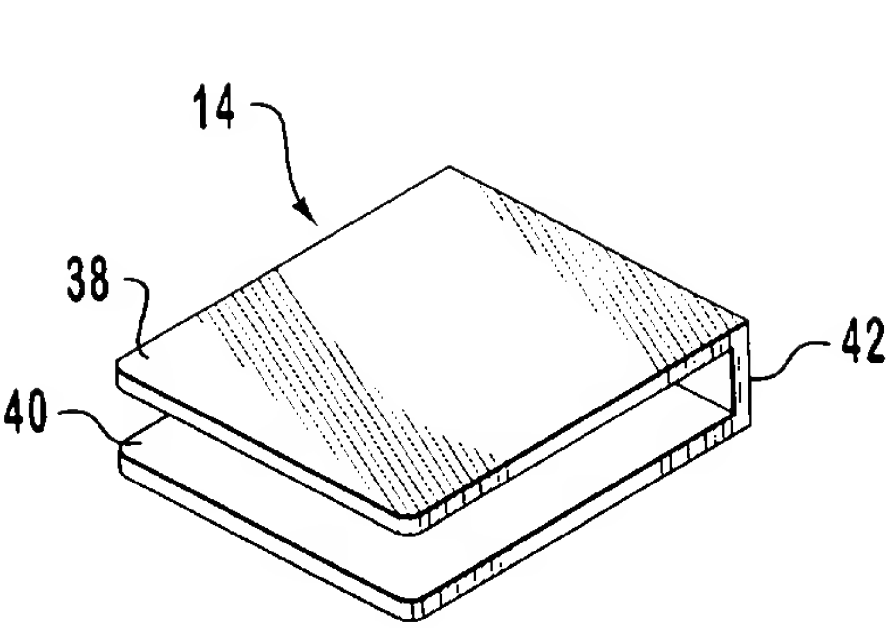


FIG. 3

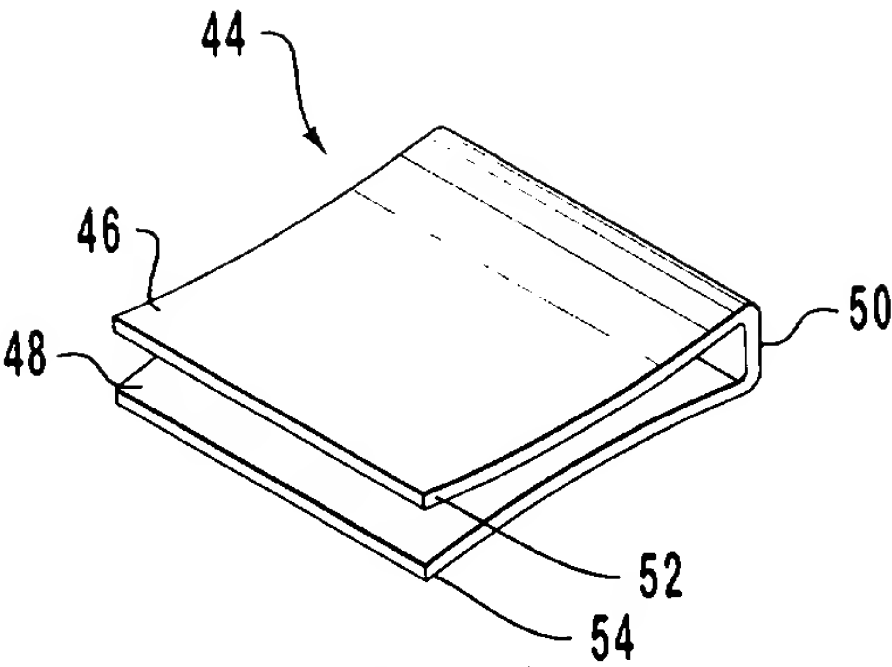


FIG. 4

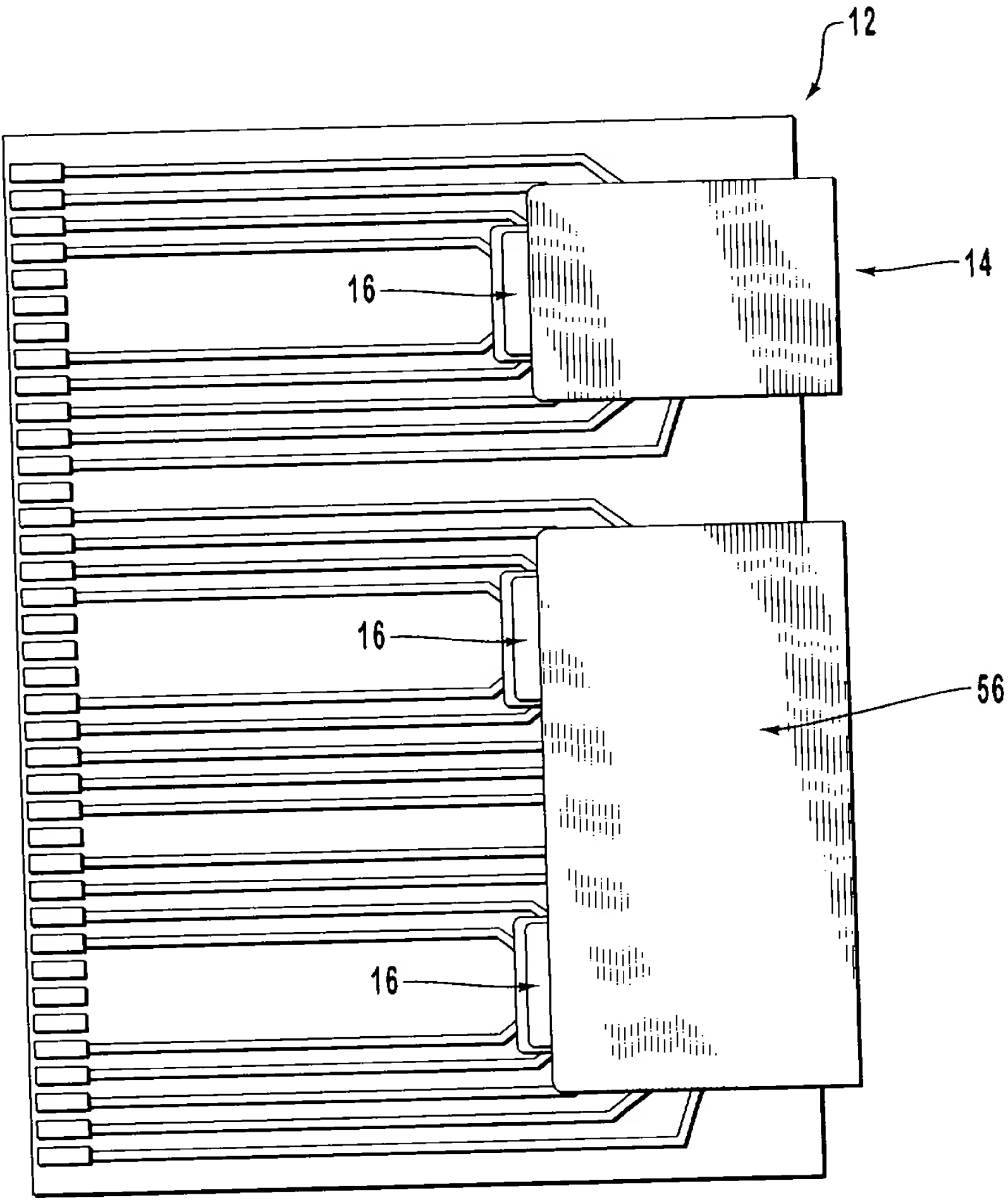


FIG. 5

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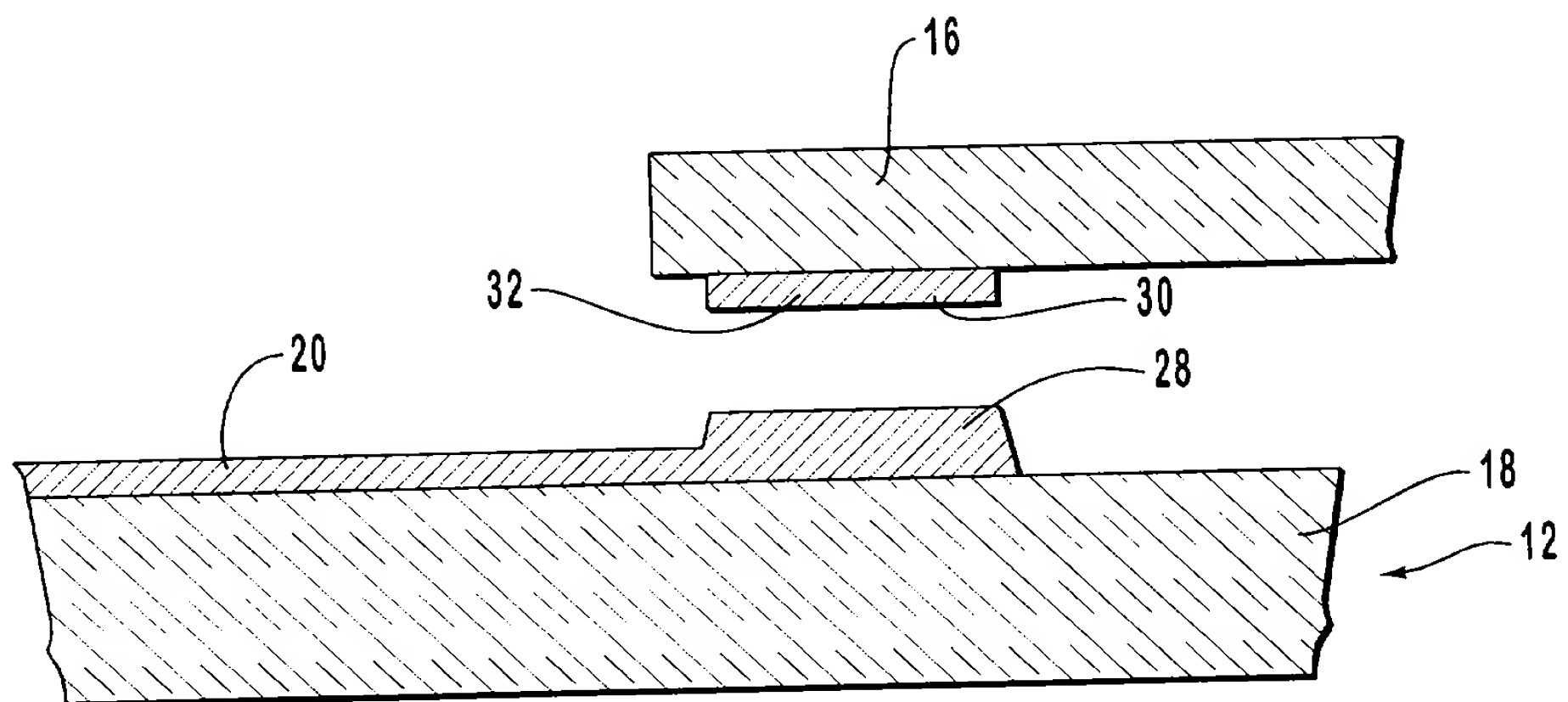


FIG. 6

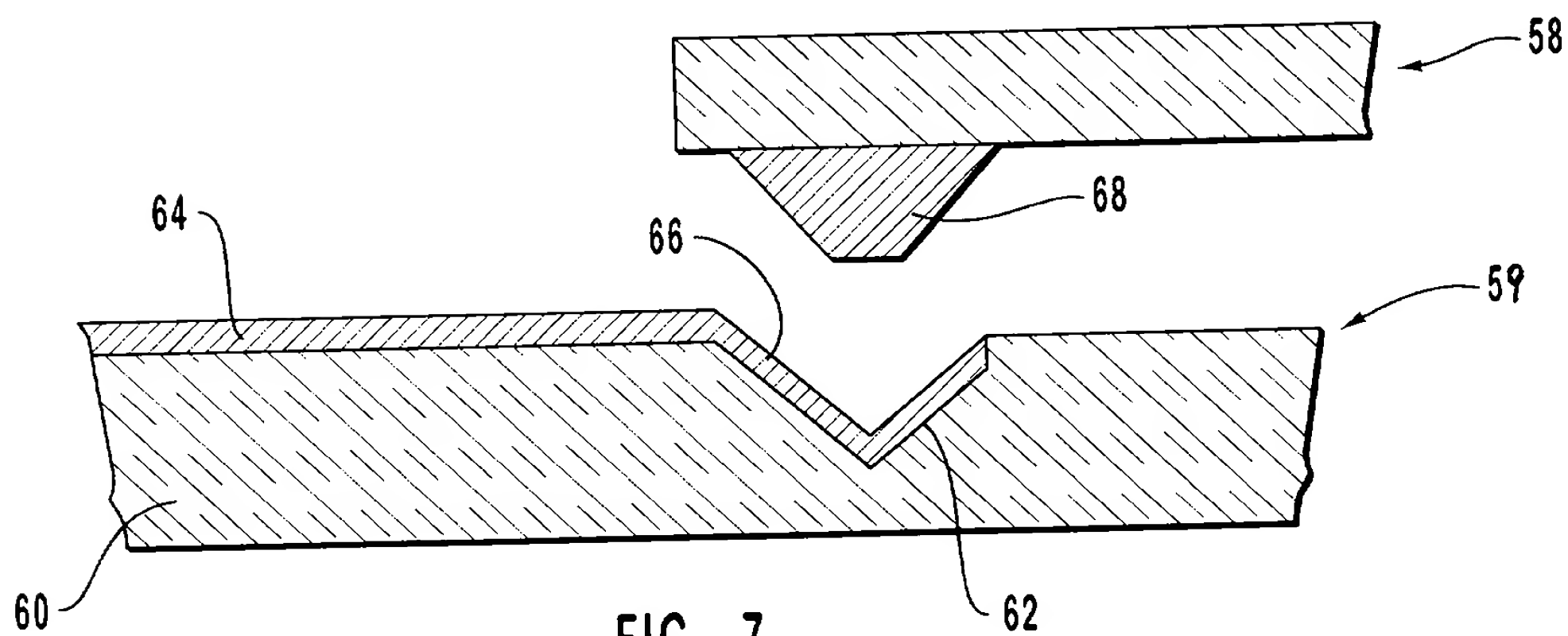


FIG. 7

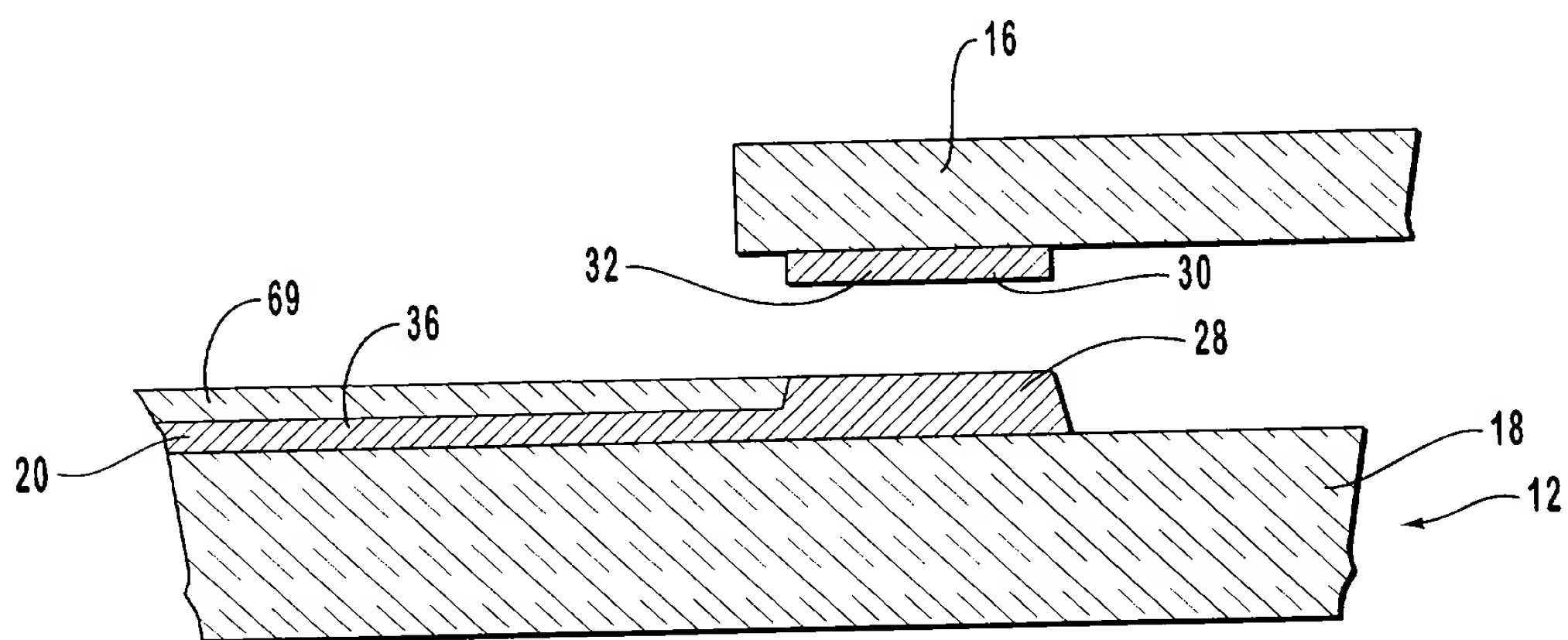
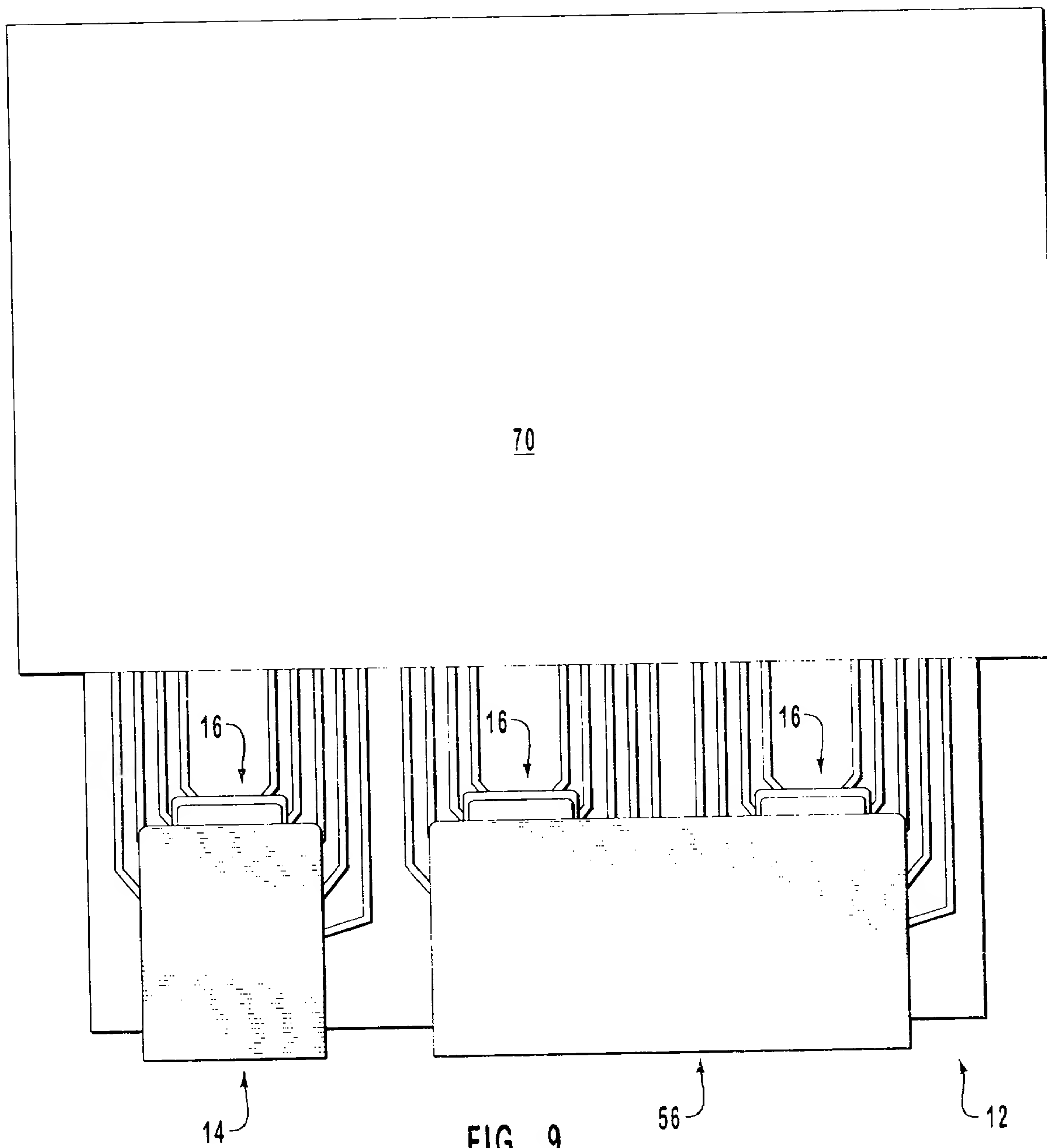


FIG. 8



DECLARATION, POWER OF ATTORNEY, AND PETITION

I, Leonard E. Mess, declare: that I am a citizen of the United States of America; that my residence and post office address is 4101 Cassia, Boise, Idaho 83705; that I verily believe I am the original, first, and sole inventor of the subject matter of the invention or discovery entitled THERMALLY CONDUCTIVE INTERPOSER AND METHOD OF USE, for which a patent is sought and which is described and claimed in the specification attached hereto; that I have reviewed and understand the contents of the above-identified specification, including the claims; and that I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Section 1.56(a) of Title 37 of the Code of Federal Regulations.

I declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful, false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful, false statements may jeopardize the validity of the application or any patent issuing thereon.

I hereby appoint as my attorneys and/or patent agents: RICK D. NYDEGGER, Registration No. 28,651; DAVID O. SEELEY, Registration No. 30,148; JONATHAN W. RICHARDS, Registration No. 29,843; JOHN C. STRINGHAM, Registration No. 40,831; MICHAEL F. KRIEGER, Registration No. 35,232; BRADLEY K. DeSANDRO, Registration No. 34,521; JOHN M. GUYNN, Registration No. 36,153; GREGORY M. TAYLOR, Registration No. 34,263; DANA L. TANGREN, Registration No. 37,246; ERIC L. MASCHOFF, Registration No. 36,596; KEVIN

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All correspondence and telephonic communications should be directed to:

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60 East South Temple
Salt Lake City, Utah 84111

Wherefore, I pray that Letters Patent be granted to me for the invention or discovery described and claimed in the foregoing specification and claims, declaration, power of attorney, and this petition.

Signed at Boise, IDAHO, this 20 day of July, 1998.

Inventor: Leonard E. Mess
Leonard E. Mess
4101 Cassia
Boise, Idaho 83705

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